

providing a substrate;
forming a conductive layer above the substrate;
forming an antireflective layer on the conductive layer;
patterning the antireflective layer and the conductive layer to form a plurality of gaps therein; and

filling the gaps with a dielectric material.

22. (New) The method of claim 21, wherein the antireflective layer includes a plurality of layers of different materials.

23. (New) The method of claim 21, wherein said filling the gaps includes filling the gaps by a high density plasma chemical vapor deposition.

24. (New) The method of claim 21, further comprising removing a portion of the antireflective layer during said filling the gaps.

25. (New) The method of claim 21, wherein said patterning includes patterning so that the profile of the patterned antireflective layer is rectangular, trapezoidal, rectangular, or rectangular having its upper corners etched away.

26. (New) The method of claim 21, further comprising forming a barrier layer between the substrate and the conductive layer.

27. (New) A method for forming isolated conductive structures on a substrate, comprising:

providing a substrate;

forming a barrier layer on the substrate;

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forming a conductive layer above the barrier layer;
forming a protective layer on the conductive layer;
patterning the protective layer and the conductive layer to form a plurality of gaps therein; and
filling the gaps with a dielectric material.

28. (New) The method of claim 27, wherein said forming a barrier includes forming the barrier layer of titanium nitride, titanium silicide or titanium-tungsten alloys.

29. (New) The method of claim 27, wherein said forming a protective layer includes forming a quarter wave plate on the conductive layer.

30. (New) The method of claim 27, wherein said patterning includes patterning the conductive layer using the protective layer as a pattern mask.

31. (New) The method of claim 27, wherein said forming a protective layer includes forming an antireflective layer and a quarter wave plate layer on the conductive layer.

32. (New) The method of claim 27, wherein said forming a protective layer includes forming the protective layer of titanium nitride, silicon oxide, silicon nitride, or oxynitride.

33. (New) The method of claim 27, further comprising partially removing the protective layer during said filling the gaps.

34. (New) The method of claim 27, wherein said filling the gaps includes filing